

ABSTRACT OF THE DISCLOSURE

5 A semiconductor structure is provided comprising a self-aligned poly-metal stack formed over a semiconductor substrate where the interface between an oxidation barrier placed over the stack and an oxidized portion of the stack lies along the sidewall of the poly-metal stack. A semiconductor structure is also provided where an etch stop layer is present in the poly region of the poly-metal stack. The present invention also relates more broadly to a memory cell array and a computer system including the poly-metal stack of the present invention.